NVF Series

2~5KV; 20~50mA; 80nS

High Voltage Rectifier Diodes

NVF Series Fast Recovery Night Vision Rectifier Diodes

Product Features

- Axial leaded connection.
- High thermal conductivity epoxy hot injection molding
- Excellent discharge characteristics.
- Fast reverse recovery time for high efficiency.
- Reverse leakage current is in the nanoampere range;
- Ultra small size packaging.

Picture

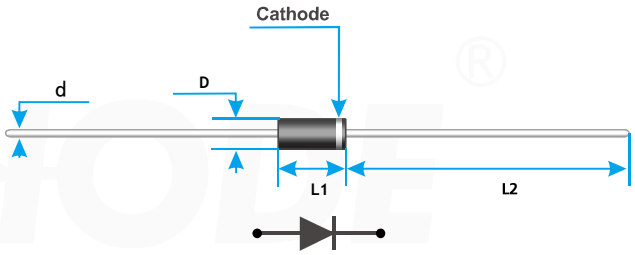
Package.No: HVD-203

Main Parameters

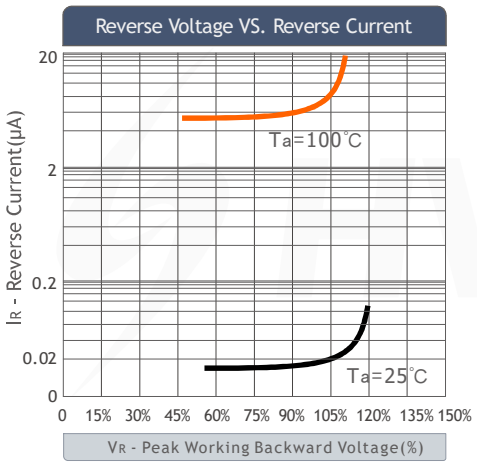
Type Code	V_{RWM} (KV)	I_F (mA)	V_F (V)	I_{FSM} (A)	T_{RR} (nS)	I_R (uA)
NV2F20	2	20	8.0	3	80	0.02
NV3F20	3	20	8.0	3	80	0.02
NV4F20	4	20	8.0	3	80	0.02
NV5F20	5	20	8.0	3	80	0.02
NV2F50	2	50	7.0	5	80	0.02
NV3F50	3	50	7.0	5	80	0.02
NV4F50	4	50	7.0	5	80	0.02
NV5F50	5	50	7.0	5	80	0.02

Dimensions

Fig.NO ❶



Curve



Package Size

Fig.NO ❶ Unit: **mm** / Inch

Package.No	D	d	L_1	L_2
HVD-203	ϕ2.0/0.079	ϕ0.5/0.02	3.0/0.118	25/0.98

About Tolerance: 【±0.2mm/0.01inch】 Except 【L2±0.5mm/0.02inch】

Other Characteristic Parameters & Test Conditions

PARAMETER NAME	SYMBOL	TEST CONDITIONS	UNIT
Max Peak Working Backward Voltage	V_{RWM}	T_A=25℃ I_R=0.02μA	KV
Average Forward Rectified Current	$I_{F(AV)}$	T_A=50℃ In air	mA
Max Forward Peak Voltage	V_F	@ T_A=25℃ I_F=I_F	V
Max Surge Forward Current	I_{FSM}	50Hz Half-sine Wave, Resistance load@T_{Break}=50℃	A
Max Reverse Recovery Time	T_{RR}	I_F = 2mA; I_R = -4mA; I_{RR} = -1mA	nS
Max Reverse Leakage Current	I_R	T_A= 25℃ V_R=V_{RWM}	uA
Junction Temperature(MAX)	T_J	-55℃~150℃	℃
Storage Temperature	T_{STG}	-55℃~125℃	℃

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ISO SGS RoHS COMPLIANT